



COPY OF PAPERS
ORIGINALLY FILED

2813
#7
Amclt
B
7-31-02
arg

Attorney Docket No. 5649-874

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Hag-ju Cho
Serial No.: 09/893,035

Group Art Unit: 2813
Examiner: Erik J. Kielin

Filed: June 27, 2001

For: METHODS OF MANUFACTURING INTEGRATED CIRCUIT DEVICES
THAT INCLUDE A METAL OXIDE LAYER DISPOSED ON ANOTHER
LAYER TO PROTECT THE OTHER LAYER FROM DIFFUSION OF
IMPURITIES AND INTEGRATED CIRCUIT DEVICES
MANUFACTURED USING SAME

Date: July 1, 2002

Box NON-FEE AMENDMENT
Commissioner for Patents
Washington, DC 20231

AMENDMENT

Sir:

This is a full and timely response to the non-final Office Action mailed April 1, 2002 that contains amendments and remarks as set forth hereafter. Attached hereto is a marked up version of the changes made to the Claims by the current amendments. The marked up version of the changes is captioned "**VERSION WITH MARKINGS TO SHOW CHANGES MADE.**"

In the Claims:

Please enter amended Claims 1, 2, and 10 as follows:

B1

Sub
C1

1. (Amended) A method of manufacturing an integrated circuit device, comprising:
forming an insulation layer that comprises oxygen between upper and lower conductive layers, the insulation layer having a first surface portion that is exposed by the upper and lower conductive layers and a second, non-exposed, surface portion; and
exposing the insulation layer to a metal precursor that is reactive with oxygen so as to form a first metal oxide layer on the first surface portion of the insulation layer without forming the first metal oxide layer on the second surface portion of the insulation layer.

RECEIVED
JUL 22 2002
TECHNOLOGY CENTER 2800